To all our customers

Regarding the change of names mentioned in the document, such as Hitachi Electric and Hitachi XX, to Renesas Technology Corp.

The semiconductor operations of Mitsubishi Electric and Hitachi were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Hitachi, Hitachi, Ltd., Hitachi Semiconductors, and other Hitachi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Renesas Technology Home Page: http://www.renesas.com

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.
   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corporation product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corporation or a third party.
2. Renesas Technology Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor for the latest product information before purchasing a product listed herein.
   The information described here may contain technical inaccuracies or typographical errors.
   Renesas Technology Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
   Please also pay attention to information published by Renesas Technology Corporation by various means, including the Renesas Technology Corporation Semiconductor home page (http://www.renesas.com).
4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
5. Renesas Technology Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
6. The prior written approval of Renesas Technology Corporation is necessary to reprint or reproduce in whole or in part these materials.
7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
   Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
8. Please contact Renesas Technology Corporation for further details on these materials or the products contained therein.

HD74ALVC16835

18-bit Universal Bus Driver with 3-state Outputs

ADE-205-192E (Z)
Preliminary
6th. Edition
January 1999

Description

The HD74ALVC16835 is an 18-bit universal bus driver designed for 2.3 V to 3.6 V V_{CC} operation.

Data flow from A to Y is controlled by output enable ($\overline{OE}$). The device operates in the transparent mode when the latch enable (LE) input is high. The A data is latched if the clock (CLK) input is held at a high or low logic level. If LE is low, the A data is stored in the latch/flip flop on the low to high transition of the CLK. When $\overline{OE}$ is high, the outputs are in the high impedance state.

To ensure the high impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup registor; the minimum value of the registor is determined by the current sinking capability of the driver.

Features

- Meets “PC SDRAM registered DIMM design support document, Rev. 1.2”
- V_{CC} = 2.3 V to 3.6 V
- Typical V_{OL} ground bounce < 0.8 V (@V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@V_{CC} = 3.3 V, Ta = 25°C)
- High output current ±24 mA (@V_{CC} = 3.0 V)

Function Table

Inputs

$\overline{OE}$	LE	CLK	A	Output Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H
L	L	H	X	Y_0 [*1]
L	L	L	X	Y_0 [*2]

H : High level

L : Low level

X : Immaterial

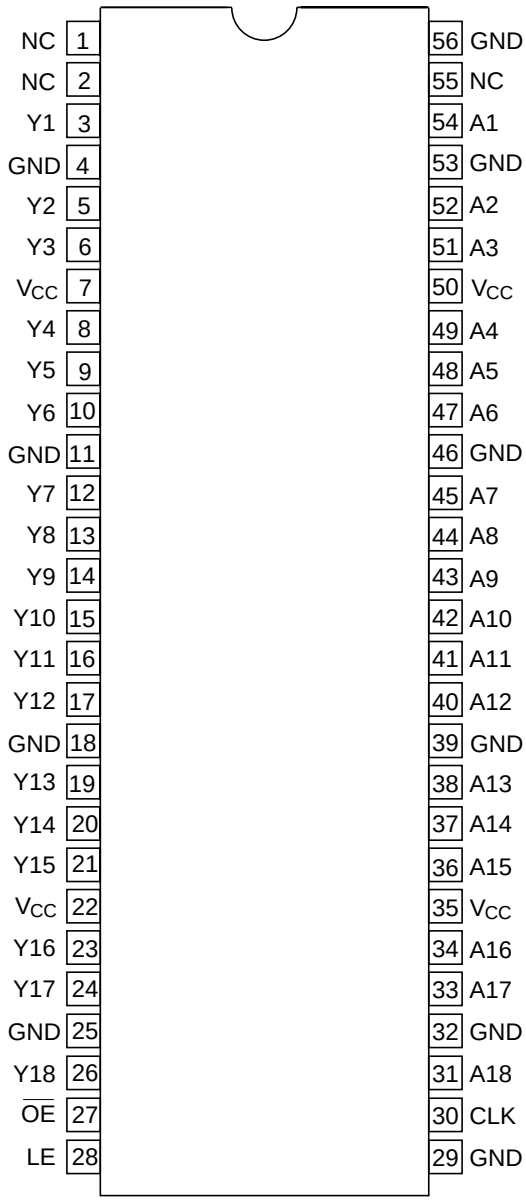
Z : High impedance

↑ : Low to high transition

Notes: 1. Output level before the indicated steady-state input conditions were established, provided that CLK was high before LE went low.

2. Output level before the indicated steady-state input conditions were established.

Pin Arrangement



(Top view)

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V_{CC}	–0.5 to 4.6	V	
Input voltage range [*1]	V_I	–0.5 to 4.6	V	
Output voltage range [*1, 2]	V_O	–0.5 to V_{CC}+0.5	V	
Input clamp current	I_{IK}	–50	mA	$V_I < 0$
Output clamp current	I_{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	±50	mA	V_O = 0 to V_{CC}
V_{CC}, GND current / pin	I_{CC} or I_{GND}	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) [*3]	P_T	1	W	TSSOP
Storage temperature range	Tstg	–65 to 150	°C	

Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating condition” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

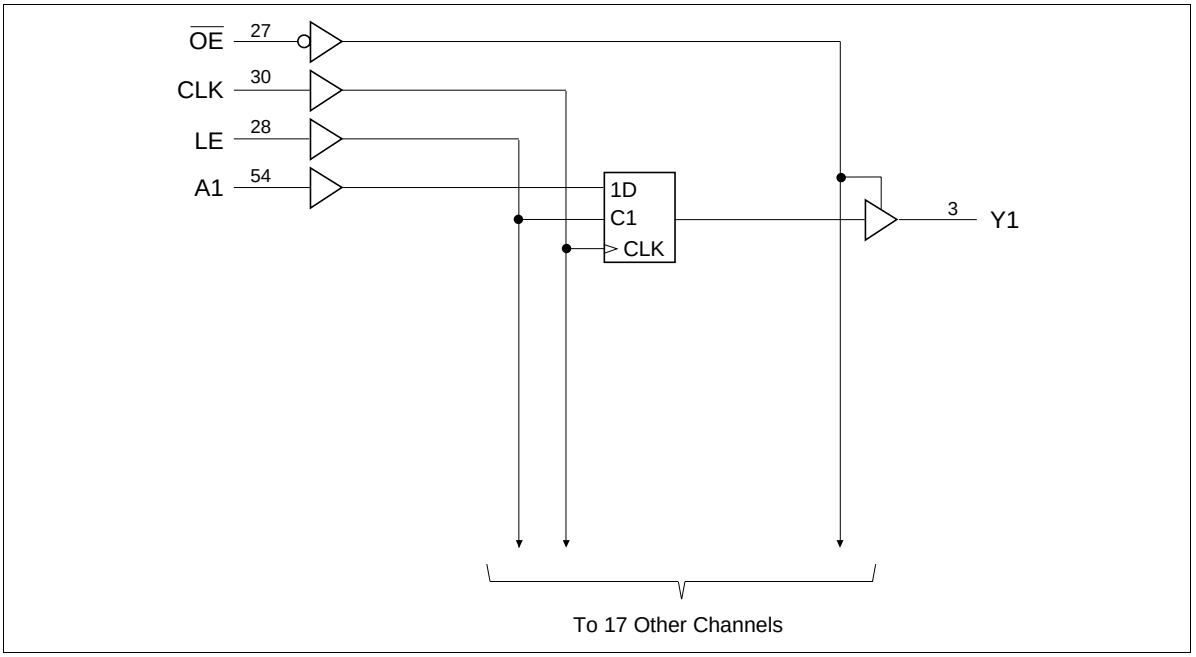
Notes: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp current ratings are observed.
2. The input and output positive-voltage ratings may be exceeded up to 4.6 V if the input and output clamp-current ratings are observed.
3. The maximum power dissipation is calculated using a junction temperature of 150°C and board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V_{CC}	2.3	3.6	V	
Input voltage	V_I	0	V_{CC}	V	
Output voltage	V_O	0	V_{CC}	V	
High-level output current	I_{OH}	—	–12	mA	V_{CC} = 2.3 V
		—	–12		V_{CC} = 2.7 V
		—	–24		V_{CC} = 3.0 V
Low-level output current	I_{OL}	—	12	mA	V_{CC} = 2.3 V
		—	12		V_{CC} = 2.7 V
		—	24		V_{CC} = 3.0 V
Input transition rise or fall rate	Δt/Δv	0	10	ns/V	
Operating free-air temperature	Ta	–40	85	°C	

Note: Unused or floating control pins must be held high or low.

Logic Diagram



Electrical Characteristics

			Ta = –40 to 85°C			
Item	**Symbol**	**V_{CC} (V)**	**Min**	**Max**	**Unit**	**Test Conditions**
Input voltage	V_{IH}	2.3 to 2.7	1.7	—	V	
		2.7 to 3.6	2.0	—		
	V_{IL}	2.3 to 2.7	—	0.7	V	
		2.7 to 3.6	—	0.8		
Output voltage	V_{OH}	2.3 to 3.6	V_{CC}–0.2	—	V	I_{OH} = –100 µA
		2.3	2.0	—		I_{OH} = –6 mA, V_{IH} = 1.7 V
		2.3	1.7	—		I_{OH} = –12 mA, V_{IH} = 1.7 V
		2.7	2.2	—		I_{OH} = –12 mA, V_{IH} = 2.0 V
		3.0	2.4	—		I_{OH} = –12 mA, V_{IH} = 2.0 V
		3.0	2.0	—		I_{OH} = –24 mA, V_{IH} = 2.0 V
	V_{OL}	2.3 to 3.6	—	0.2	V	I_{OL} = 100 µA
		2.3	—	0.4		I_{OL} = 6 mA, V_{IL} = 0.7 V
		2.3	—	0.7		I_{OL} = 12 mA, V_{IL} = 0.7 V
		2.7	—	0.4		I_{OL} = 12 mA, V_{IL} = 0.8 V
		3.0	—	0.55		I_{OL} = 24 mA, V_{IL} = 0.8 V
Input current	I_{IN}	3.6	—	±5.0	µA	V_{IN} = V_{CC} or GND
Off state output current	I_{OZ}	3.6	—	±10	µA	V_{OUT} = V_{CC} or GND
Quiescent supply current	I_{CC}	3.6	—	40	µA	V_{IN} = V_{CC} or GND
	ΔI_{CC}	3.0 to 3.6	—	750	µA	One input at (V_{CC}–0.6)V, other inputs at V_{CC} or GND

Switching Characteristics (Ta = –40 to 85°C)

Item	Symbol	V_{cc} (V)	Min	Typ	Max	Unit	From (Input)	To (Output)
Maximum clock frequency	f_{max}	2.5±0.2	150	—	—	MHz		
		2.7	150	—	—			
		3.3±0.3	150	—	—			
Propagation delay time	t_{PLH}	2.5±0.2	1.0	—	4.2	ns	A	Y
	t_{PHL}	2.7	—	—	4.2			
		3.3±0.3	1.0	—	3.6			
		2.5±0.2	1.3	—	5.0		LE	Y
		2.7	—	—	4.9			
		3.3±0.3	1.3	—	4.2			
		2.5±0.2	1.4	—	5.5		CLK	Y
		2.7	—	—	5.2			
		3.3±0.3	1.4	—	4.5			
Output enable time	t_{ZH}	2.5±0.2	1.4	—	5.5	ns	$\overline{OE}$	Y
	t_{ZL}	2.7	—	—	5.6			
		3.3±0.3	1.1	—	4.6			
Output disable time	t_{HZ}	2.5±0.2	1.0	—	4.5	ns	$\overline{OE}$	Y
	t_{LZ}	2.7	—	—	4.3			
		3.3±0.3	1.3	—	3.9			
Input capacitance	C_{IN}	3.3	3.0	4.5	7.0	pF	Control inputs	
		3.3	3.0	6.0	9.0		Data inputs	
Output capacitance	C_O	3.3	3.0	7.0	9.0	pF	Y ports	

Switching Characteristics (Ta = –40 to 85°C) (cont)

Item	Symbol	V_{cc} (V)	Min	Typ	Max	Unit	From (Input)
Setup time	t_{su}	2.5±0.2	2.2	—	—	ns	Data before CLK↑
		2.7	2.1	—	—		
		3.3±0.3	1.7	—	—		
		2.5±0.2	1.9	—	—		Data before LE↓
		2.7	1.6	—	—		CLK “H”
		3.3±0.3	1.5	—	—		
		2.5±0.2	1.3	—	—		Data before LE↓
		2.7	1.1	—	—		CLK “L”
		3.3±0.3	1.0	—	—		
Hold time	t_h	2.5±0.2	0.6	—	—	ns	Data after CLK↑
		2.7	0.6	—	—		
		3.3±0.3	0.7	—	—		
		2.5±0.2	1.4	—	—		Data after LE↓
		2.7	1.7	—	—		CLK “H” or “L”
		3.3±0.3	1.4	—	—		
Pulse width	t_w	2.5±0.2	3.3	—	—	ns	LE “H”
		2.7	3.3	—	—		
		3.3±0.3	3.3	—	—		
		2.5±0.2	3.3	—	—		CLK “H” or “L”
		2.7	3.3	—	—		
		3.3±0.3	3.3	—	—		

Switching Characteristics (Ta = 0 to 85°C)

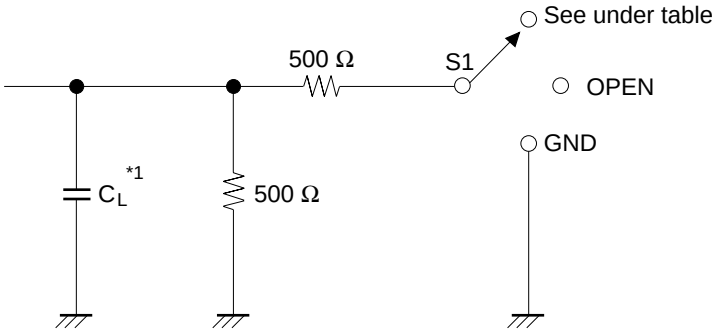
Item		Symbol	V_{cc} (V)	Min	Typ	Max	Unit	FROM (Input)	TO (Output)
Propagation	C_L=0pF [*1]	t_{PLH}, t_{PHL}	3.3±0.165	0.9	—	2.0	ns	A	Y
delay time	C_L=50pF		3.3±0.165	1.0	—	4.5			
	C_L=0pF [*1]		3.3±0.165	1.5	—	3.0		CLK	Y
	C_L=50pF		3.3±0.165	1.7	—	4.5			
	C_L=50pF	t_{SSO} [*1, 2]	3.3±0.165	1.7	—	4.8		CLK, A	Y
Output rise / fall time	C_L=50pF	t_{TLH}, t_{THL} [*1]	3.3±0.165	1.0	—	2.5	volts/ ns		Y

Notes: 1. This parameter is characterized but not tested.
2. t_{SSO} : Simultaneous switching output time.

Operating Characteristics (Ta = 25°C)

Item		Symbol	V_{CC} = 2.5±0.2 V	V_{CC} = 3.3±0.3 V	Unit	Test Conditions
			Typ	Typ		
Power dissipation capacitance	Outputs enable	C_{pd}	22.0	24.5	pF	C_L = 0, f = 10 MHz
	Outputs disable		5.0	6.0		

Test Circuit

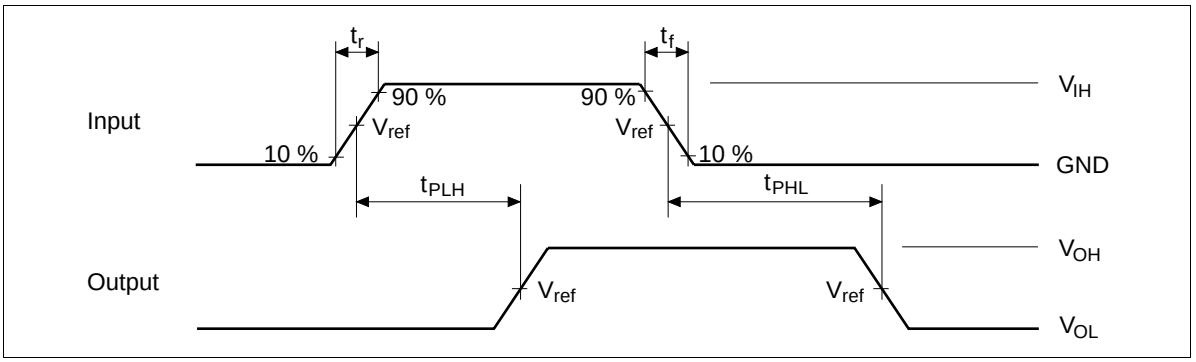


Load Circuit for Outputs

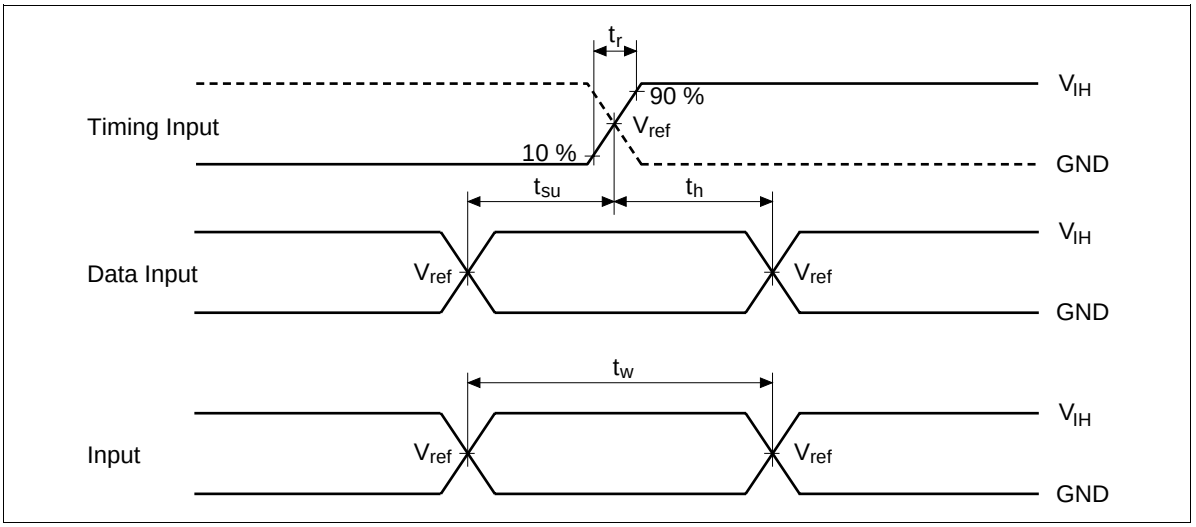
Symbol	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
t_{PLH} / t_{PHL}	OPEN	OPEN
t_{su} / t_h / t_w		
t_{ZH} / t_{HZ}	GND	GND
t_{ZL} / t_{LZ}	2 × V_{CC}	6.0 V
C_L	30 pF	50 pF

Note: 1. C_L includes probe and jig capacitance.

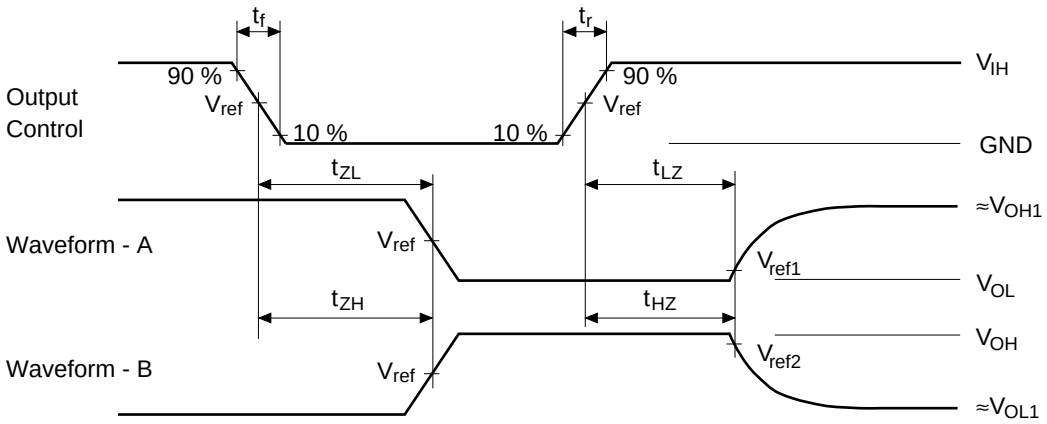
Waveforms – 1



Waveforms – 2



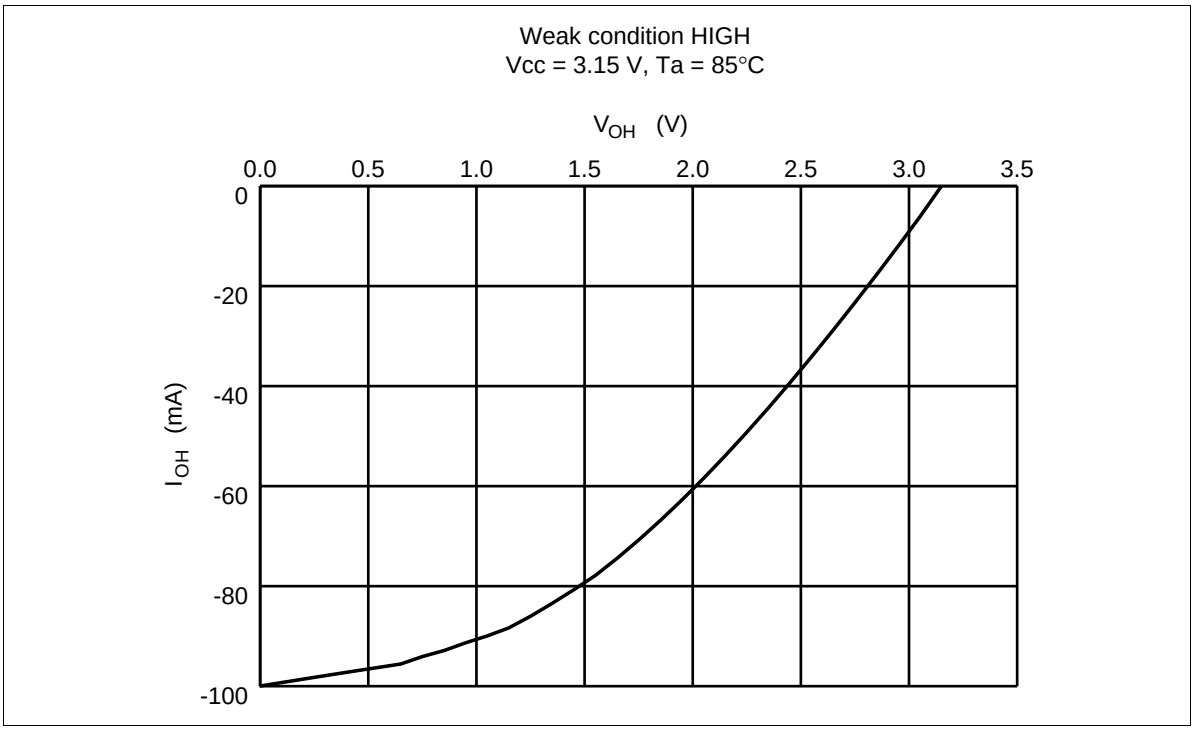
Waveforms – 3

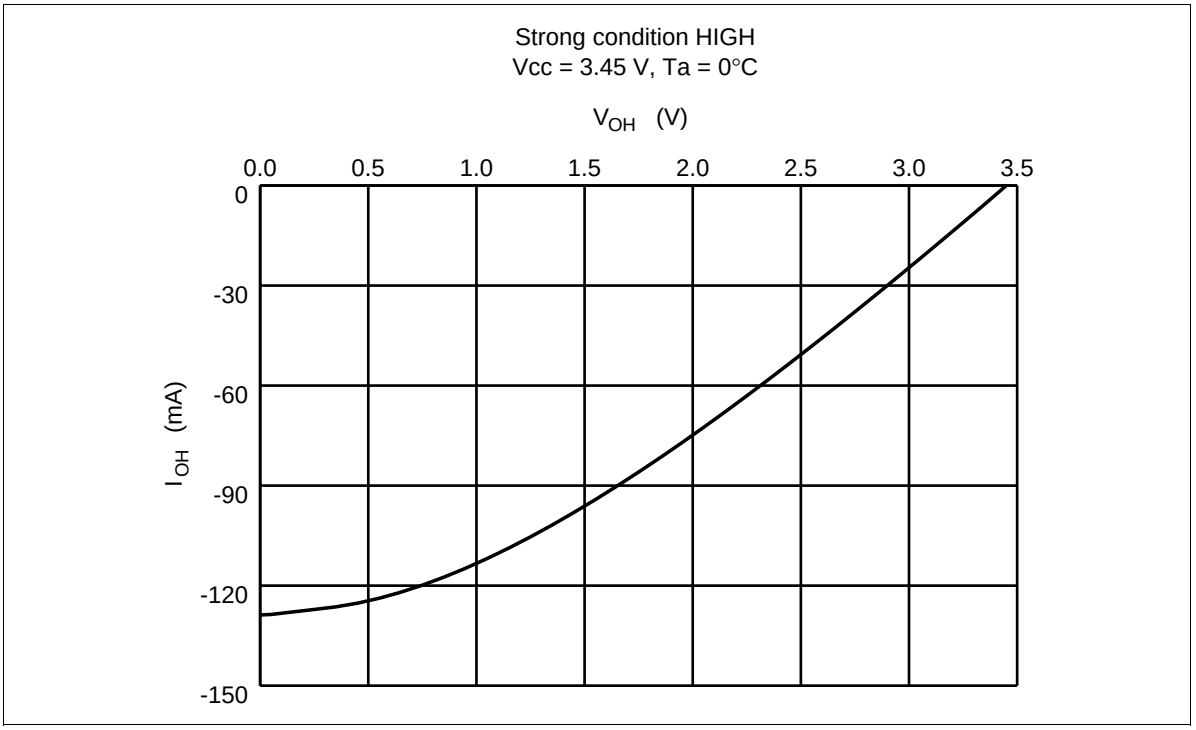


TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
V_{IH}	V_{CC}	2.7 V
V_{ref}	1/2 V_{CC}	1.5 V
V_{ref1}	V_{OL} +0.15 V	V_{OL} +0.3 V
V_{ref2}	V_{OH}–0.15 V	V_{OH}–0.3 V
V_{OH1}	V_{CC}	3.0 V
V_{OL1}	GND	GND

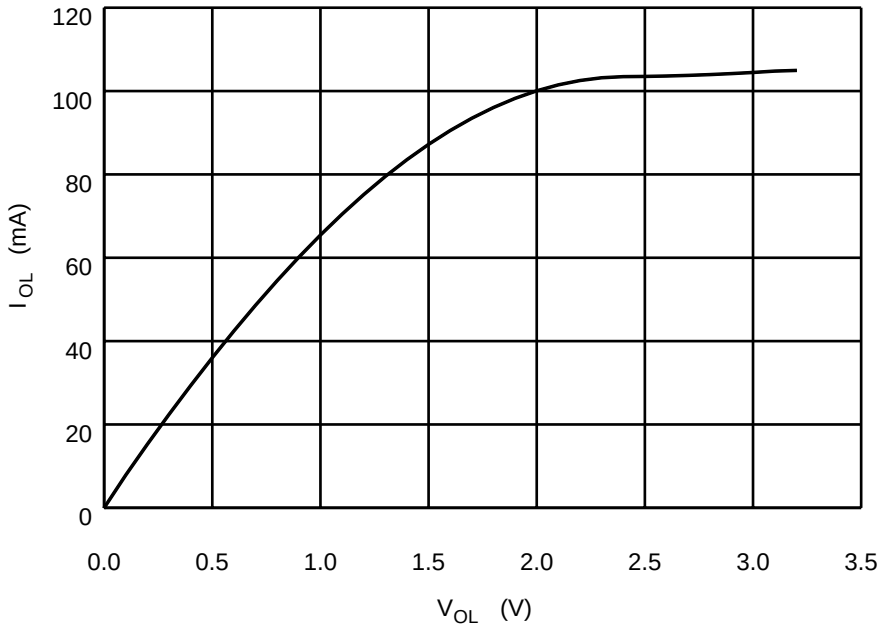
Notes:
1. All input pulses are supplied by generators having the following characteristics :
   PRR ≤ 10 MHz, Zo = 50 Ω, t_r ≤ 2.0 ns, t_f ≤ 2.0 ns. (V_{CC} = 2.5±0.2 V)
   PRR ≤ 10 MHz, Zo = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns. (V_{CC} = 2.7 V, 3.3±0.3 V)
2. Waveform–A is for an output with internal conditions such that the output is low except when disabled by the output control.
3. Waveform–B is for an output with internal conditions such that the output is high except when disabled by the output control.
4. The outputs are measured one at a time with one transition per measurement.

IV Characteristics for Register Output (Measured value)

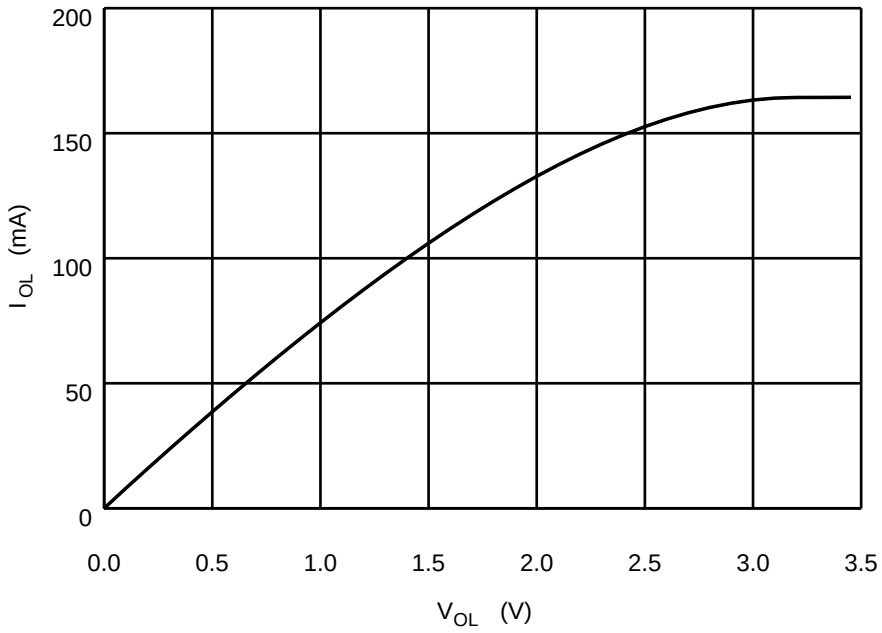




Weak condition LOW
Vcc = 3.15 V, Ta = 85°C

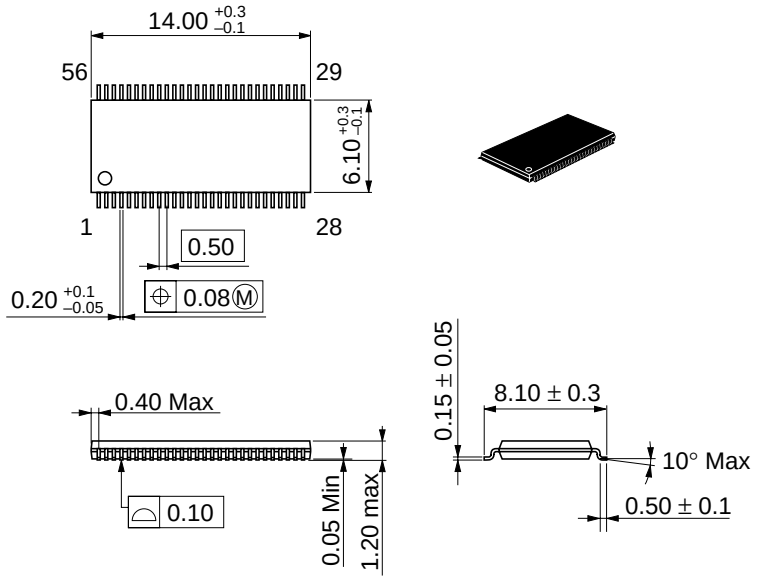


Strong condition LOW
Vcc = 3.45 V, Ta = 0°C



Package Dimensions

Unit : mm



Hitachi code	TTP-56D
EIAJ code	—
JEDEC code	—

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL
NorthAmerica : http:semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
Asia (Singapore) : http://www.has.hitachi.com.sg/grp3/sicd/index.htm
Asia (Taiwan) : http://www.hitachi.com.tw/E/Product/SICD_Frame.htm
Asia (HongKong) : http://www.hitachi.com.hk/eng/bo/grp3/index.htm
Japan : http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor
(America) Inc.
2000 Sierra Point Parkway
Brisbane, CA 94005-1897
Tel: <1> (800) 285-1601
Fax: <1> (303) 297-0447

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX